

# STL128D

### High voltage fast-switching NPN power transistor

#### Features

- High voltage capability
- Low spread of dynamic parameters
- Very high switching speed
- Integrated antiparallel collector-emitter diode

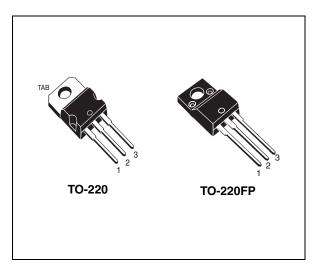
### Applications

- Electronic ballast for fluorescent lighting
- Flyback and forward single transistor low power converters

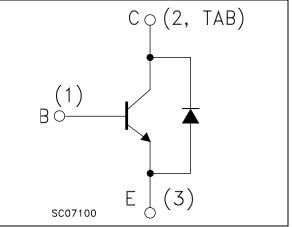
### Description

These devices are high voltage fast-switching NPN power transistors. They are manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability.

They use a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA. The devices are designed for use in lighting applications and low cost switch-mode power supplies.



#### Figure 1. Internal schematic diagram



#### Table 1.Device summary

Order codes	Marking	Packages	Packaging
STL128D	L128D	TO-220	Tube
STL128DFP	L128DFP	TO-220FP	Tube

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# 1 Electrical ratings

Table 2. Absolute maximum rating	Table 2. Abs	olute maximum	ratings
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Symbol	Parameter	Va	Unit	
Symbol	Falameter	TO-220	TO-220FP	Omt
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> = 0) 700		V	
V <sub>CEO</sub>	Collector-emitter voltage ( $I_B = 0$ )	40	00	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	V <sub>(BF</sub>	R)EBO	V
۱ <sub>C</sub>	Collector current 4		А	
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms) 8		А	
Ι <sub>Β</sub>	Base current 2		А	
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5 ms) 4		А	
V <sub>ISOL</sub>	Insulation withstand voltage (RMS) from all three 150 150 150 150 150 150 150 150 150 150		1500	V
P <sub>TOT</sub>	Total dissipation at $T_c = 25 \text{ °C}$	65	30	W
T <sub>stg</sub>	Storage temperature		-65 to 150	
TJ	Max. operating junction temperature 150		°C	

Table 3. Thermal d
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Symbol	Parameter	Value		Unit
Symbol	Falameter	TO-220	TO-220FP	Unit
R <sub>thJ-case</sub>	Thermal resistance junction-case max	1.92	4.17	°C/W
R <sub>thJ-amb</sub>	Thermal resistance junction-ambient max	62	2.5	°C/W



### 2 Electrical characteristics

 $T_{case}$  = 25 °C unless otherwise specified

Symbol	Parameter	Test co	nditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 700 V V <sub>CE</sub> = 700 V	T <sub>c</sub> = 125 °C			100 500	μΑ μΑ
I <sub>CEO</sub>	Collector cut-off current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 400 V				250	μA
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 mA		9		18	V
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage $(I_B = 0)$	I <sub>C</sub> = 100 mA		400			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{C} = 1 A$ $I_{C} = 2.5 A$ $I_{C} = 3.5 A$	I <sub>B</sub> = 0.2 A I <sub>B</sub> = 0.5 A I <sub>B</sub> = 0.7 A		0.5	1 1.5	V V V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 1 A I <sub>C</sub> = 2.5 A	I <sub>B</sub> = 0.2 A I <sub>B</sub> = 0.5 A			1.2 1.3	V V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$I_{\rm C} = 10 \text{ mA}$ $I_{\rm C} = 2 \text{ A}$	V <sub>CE</sub> = 5 V V <sub>CE</sub> = 5 V	10 10		32	
t <sub>s</sub> t <sub>f</sub>	Inductive load Storage time Fall time	$V_{CC} = 200 V$ $I_{B1} = 0.4 A$ $R_{BB} = 0$	$I_C=2 A$ $V_{BE(off)} = -5 V$ $L = 200 \mu H$		0.6 0.1		μs μs

 Table 4.
 Electrical characteristics

1. Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  1.5 %.



#### 2.1 Electrical characteristics (curves)

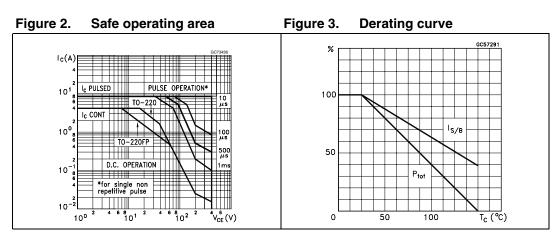
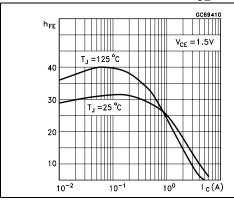
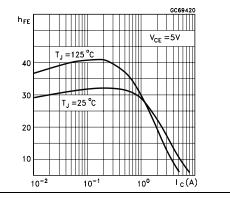
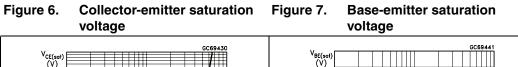
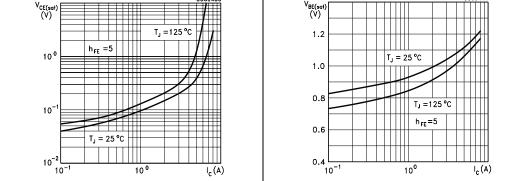


Figure 4. DC current gain ( $V_{CE} = 1.5 V$ ) Figure 5. DC current gain ( $V_{CE} = 5 V$ )











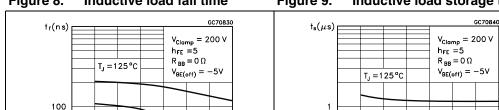
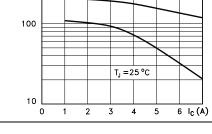
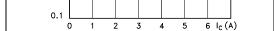


Figure 8. Inductive load fall time Figure 9. Inductive load storage time





4 5 6 I<sub>C</sub>(A)

T<sub>J</sub> =25 °C

0 1 2



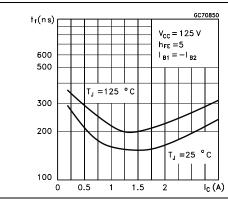
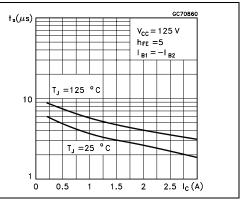
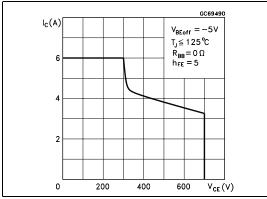
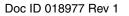


Figure 11. **Resistive load storage time** 











### 3 Package mechanical data

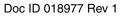
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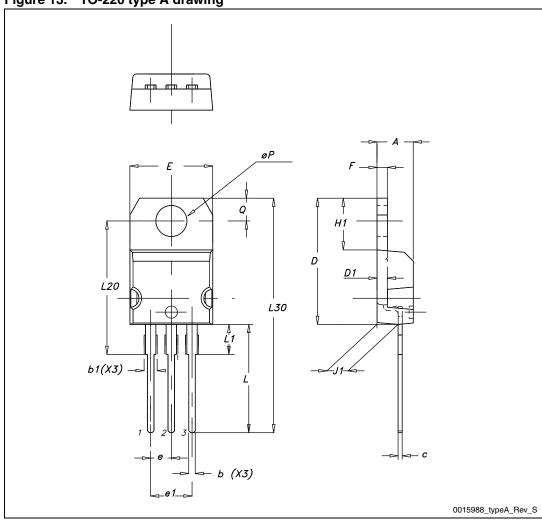


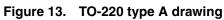
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Table 5.	TO-220 type A mechanical data	
		mm

Dim.		mm	
Dini.	Min.	Тур.	Max.
А	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
с	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØР	3.75		3.85
Q	2.65		2.95





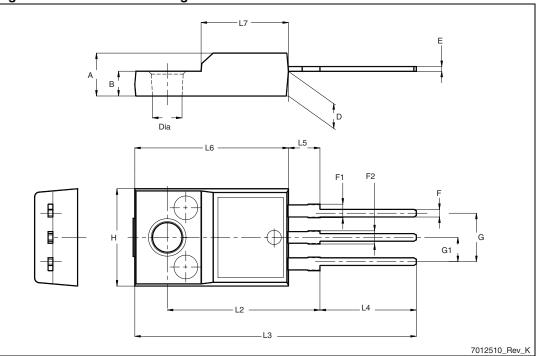




Dim		mm.	
Dim.	Min.	Тур.	Max.
А	4.4		4.6
В	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
Н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Table 6. TO-220FP mechanical data

Figure 14. TO-220FP drawing



Doc ID 018977 Rev 1



## 4 Revision history

#### Table 7.Document revision history

Date	Revision	Changes
27-Jun-2011	1	First release



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